

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

# 2SC5549

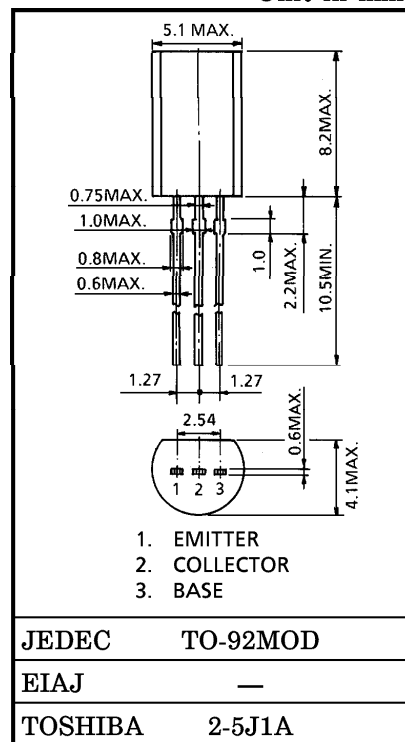
HIGH SPEED SWITCHING APPLICATION FOR INVERTER LIGHTING SYSTEM

Unit in mm

- Suitable for  $R_{CC}$  Circuit. (Guaranteed small current  $h_{FE}$ )  
:  $h_{FE}=13$  (Min.) ( $I_C=1mA$ )
- High Speed :  $t_r=0.5\mu s$  (Max.),  $t_f=0.3\mu s$  (Max.) ( $I_C=0.24A$ )
- High Voltage :  $V_{CEO}=400V$

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	400	V
Collector-Emitter Voltage	$V_{CEO}$	400	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Collector Current	DC	$I_C$	1
	Pulse	$I_{CP}$	2
Base Current	$I_B$	0.5	A
Collector Power Dissipation	$P_C$	0.9	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$



Weight : 0.36g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB} = 320V, I_E = 0$	—	—	100	$\mu A$
Emitter Cut-off Current		$I_{EBO}$	$V_{EB} = 7V, I_C = 0$	—	—	100	$\mu A$
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	$I_C = 1mA, I_B = 0$	400	—	—	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	400	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5V, I_C = 1mA$	13	—	—	
		$h_{FE(2)}$	$V_{CE} = 5V, I_C = 0.04A$	20	—	65	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 0.2A, I_B = 25mA$	—	—	1.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 0.2A, I_B = 25mA$	—	—	1.3	V
Switching Time	Rise Time	$t_r$	<p> <math>20\mu s</math> <math>V_{CC} = 200V</math>  <math>I_{B1}</math> <math>I_{B2}</math> <math>I_C</math> <math>833\Omega</math>              INPUT OUTPUT  <math>I_{B1} = 0.03A, I_{B2} = -0.06A</math>              DUTY CYCLE <math>\leq 1\%</math> </p>	—	—	0.5	$\mu s$
	Storage Time	$t_{stg}$		—	—	5.0	
	Fall Time	$t_f$		—	—	0.3	

